

# Nobuhiko Ozaki

## List of Publications by Year in descending order

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112  
papers

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citations

430442

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112  
docs citations

112  
times ranked

863  
citing authors

#	ARTICLE	IF	CITATIONS
1	Near-infrared dual-wavelength surface-emitting light source using InAs quantum dots resonant with vertical cavity modes. Japanese Journal of Applied Physics, 2022, 61, SD1003.	0.8	0
2	In-situ estimation of emission wavelength of embedded InAs QDs using RHEED intensity measurements. Journal of Crystal Growth, 2022, 588, 126657.	0.7	2
3	1.1 $\mu$ m waveband tunable laser using emission-wavelength-controlled InAs quantum dots for swept-source optical coherence tomography applications. Japanese Journal of Applied Physics, 2021, 60, SBBE02.	0.8	3
4	Emission wavelength control of InAs/GaAs quantum dots using an As <sub>2</sub> source for near-infrared broadband light source applications. Applied Physics Express, 2021, 14, 055501.	1.1	1
5	Bandwidth enhancement in an InGaN/GaN three-section superluminescent diode for optical coherence tomography. Applied Physics Letters, 2020, 117, .	1.5	3
6	Numerical investigation of highly efficient and tunable terahertz-wave generation using a low-group-velocity and low-dispersion two-dimensional GaAs photonic crystal waveguide. Japanese Journal of Applied Physics, 2020, 59, 090903.	0.8	3
7	Development of a broadband superluminescent diode based on self-assembled InAs quantum dots and demonstration of high-axial-resolution optical coherence tomography imaging. Journal Physics D: Applied Physics, 2019, 52, 225105.	1.3	15
8	Preparation of Ag <sub>2</sub> Se QDs with excellent aqueous dispersion stability by organic coating with aqueous ATRP. Polymer Bulletin, 2019, 76, 4753-4768.	1.7	0
9	Tunable external cavity laser diode based on wavelength controlled self-assembled InAs quantum dots for swept-source optical coherence tomography applications at 1100 nm wavelength band. , 2019, , .		5
10	Development of a Broadband Superluminescent Diode Based on Self-Assembled Quantum Dots for Optical Coherence Tomography Applications. The Review of Laser Engineering, 2019, 47, 578.	0.0	0
11	Non-destructive and non-contact measurement of semiconductor optical waveguide using optical coherence tomography with a visible broadband light source. Japanese Journal of Applied Physics, 2018, 57, 08PE03.	0.8	2
12	Growth of quantum three-dimensional structure of InGaAs emitting at $\sim 1 \mu$ m applicable for a broadband near-infrared light source. Journal of Crystal Growth, 2017, 477, 230-234.	0.7	6
13	Gallium nitride light sources for optical coherence tomography. , 2017, , .		9
14	Ultra-small near-infrared multi-wavelength light source using a heterojunction photonic crystal waveguide and self-assembled InAs quantum dots. Japanese Journal of Applied Physics, 2017, 56, 050303.	0.8	7
15	Gallium Nitride Superluminescent Light Emitting Diodes for Optical Coherence Tomography Applications. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-11.	1.9	21
16	Strain Balancing of Metal-Organic Vapour Phase Epitaxy InAs/GaAs Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-8.	1.9	5
17	Non-destructive inspection of semiconductor optical waveguide using optical coherence tomography with visible broadband light source. , 2017, , .		2
18	Superluminescent diode with a broadband gain based on self-assembled InAs quantum dots and segmented contacts for an optical coherence tomography light source. Journal of Applied Physics, 2016, 119, 083107.	1.1	23

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19	Operation of an InAs quantum-dot embedded GaAs photonic crystal slab waveguide laser by using two-photon pumping for photonics integrated circuits. AIP Advances, 2016, 6, 065215.	0.6	9
20	Emission wavelength variation of InAs quantum dots grown on GaAs using As <sub>2</sub> molecules in molecular beam epitaxy. , 2016, , .		0
21	High-resolution and nondestructive profile measurement by spectral-domain optical coherence tomography with a visible broadband light source for optical-device fabrication. Japanese Journal of Applied Physics, 2016, 55, 08RE05.	0.8	5
22	Electrically Driven Near-Infrared Broadband Light Source with Gaussian-Like Spectral Shape Based on Multiple InAs Quantum Dots. IEICE Transactions on Electronics, 2016, E99.C, 381-384.	0.3	8
23	Imaging of spectral-domain optical coherence tomography using a superluminescent diode based on InAs quantum dots emitting broadband spectrum with Gaussian-like shape. Japanese Journal of Applied Physics, 2015, 54, 04DG07.	0.8	16
24	Spectral-domain optical coherence tomography with a white light developed for optical device fabrication. , 2015, , .		0
25	Spectral and temporal photoluminescence behavior of colloidal PbS quantum dots. Superlattices and Microstructures, 2015, 79, 123-134.	1.4	4
26	Optical characterization of In-flushed InAs/GaAs quantum dots emitting a broadband spectrum with multiple peaks at $\sim 1.1\ \mu\text{m}$ . Nanoscale Research Letters, 2015, 10, 231.	3.1	8
27	Broadband Gain Superluminescent Diode Based on Self-assembled InAs Quantum Dots with Segmented Contacts. , 2015, , .		0
28	Integration of Emission-Wavelength-Controlled InAs Quantum Dots for Ultra-Broadband Near-Infrared Light Source. Nanomaterials and Nanotechnology, 2014, 4, 26.	1.2	18
29	Near-infrared superluminescent diode using stacked self-assembled InAs quantum dots with controlled emission wavelengths. Japanese Journal of Applied Physics, 2014, 53, 04EG10.	0.8	21
30	Alcohol additive effect in hydrogen generation from water with carbon by photochemical reaction. Japanese Journal of Applied Physics, 2014, 53, 05FZ03.	0.8	8
31	Optical Coherence Tomography Imaging by Using a Superluminescent Diode Based on InAs/GaAs Quantum Dots. , 2014, , .		0
32	Hydrogen Generation by Laser Irradiation of Carbon Powder in Water. Journal of Physical Chemistry C, 2013, 117, 18281-18285.	1.5	24
33	Extending emission wavelength of InAs/GaAs quantum dots beyond $1.3\ \mu\text{m}$ by using quantum dot bi-layer for broadband light source. Journal of Crystal Growth, 2013, 378, 553-557.	0.7	11
34	Growth of InAs/GaAs quantum dots with central emission wavelength of $1.05\ \mu\text{m}$ using In-flush technique for broadband near-infrared light source. Journal of Crystal Growth, 2013, 378, 501-505.	0.7	13
35	Monolithically grown multi-color InAs quantum dots as a spectral-shape-controllable near-infrared broadband light source. Applied Physics Letters, 2013, 103, .	1.5	15
36	Enhancement upconversion luminescence in InAs-quantum dots embedded GaAs photonic-crystal slab line-defect waveguide. , 2013, , .		0

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37	Broadband emission centered at $\lambda = 1.1 \mu\text{m}$ with a Gaussian-like spectrum by stacking In-flashed QD layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 1361-1364.	0.8	5
38	Growth and Optical Characterizations of InAs-QDs Emitting at $1.1 \mu\text{m}$ with a Broadband Spectrum for a Light Source for Biomedical Optical Coherence Tomography. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2013, 62, 679-682.	0.1	0
39	Broadband near-infrared superluminescent diode based on stacked multi-color InAs/GaAs quantum dots. , 2013, , .		0
40	Formation of Nanoparticles of Organic Molecules by Liquid Laser Ablation. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1455, 49.	0.1	2
41	Modification of optical response in quantum dots embedded in a photonic crystal waveguide via photonic band engineering. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1438, 29.	0.1	1
42	Size dependent optical properties of quinacridonequinone nanoparticles prepared by liquid laser ablation in water. <i>Chemical Physics Letters</i> , 2012, 552, 102-107.	1.2	7
43	Broadband Light Source Based on Four-Color Self-Assembled InAs Quantum Dot Ensembles Monolithically Grown in Selective Areas. <i>IEICE Transactions on Electronics</i> , 2012, E95-C, 247-250.	0.3	6
44	Nanophotonics Based on Semiconductor-Photonic Crystal/Quantum Dot and Metal-/Semiconductor-Plasmonics. <i>IEICE Transactions on Electronics</i> , 2012, E95-C, 178-187.	0.3	0
45	Multi-color quantum dot ensembles grown in selective-areas for shape-controlled broadband light source. <i>Journal of Crystal Growth</i> , 2011, 323, 191-193.	0.7	10
46	InAs quantum-dots laser utilizing GaAs W1 type photonic-crystal slab line-defect waveguide. , 2011, , .		1
47	Selective-area growth of 4-color InAs-QD ensembles for broadband light source. , 2011, , .		0
48	Photonic crystal all-optical switches. , 2010, , 241-275.		1
49	Evolution of nanophotonics from semiconductor photonic crystal device to metal/semiconductor plasmonic device. , 2010, , .		1
50	Nanophotonics technology for advanced quantum dot/photonic crystal device and metal/semiconductor plasmonic device. , 2010, , .		0
51	WIDEBAND OPERATION OF 2D PHOTONIC CRYSTAL DIRECTIONAL COUPLER WITH TOPOLOGY OPTIMIZED WAVEGUIDE BENDS. <i>Journal of Nonlinear Optical Physics and Materials</i> , 2010, 19, 543-550.	1.1	3
52	Nanophotonic technologies for innovative all-optical signal processor using photonic crystals and quantum dots. , 2009, , .		0
53	Photonic Crystal and Quantum Dot Technologies for Ultra-small and Ultra-fast All-optical Flip-flop. <i>ECS Transactions</i> , 2009, 16, 31-37.	0.3	0
54	Monolithic Fabrication of Two-Color InAs Quantum Dots for Integrated Optical Devices by Using a Rotational Metal Mask. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 065502.	0.8	6

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55	Advanced quantum dot and photonic crystal technologies for integrated nanophotonic circuits. <i>Microelectronics Journal</i> , 2009, 40, 736-740.	1.1	5
56	Site-controlled InAs quantum dot formation grown on the templates fabricated by the Nano-Jet Probe method. <i>Journal of Crystal Growth</i> , 2009, 311, 1819-1821.	0.7	7
57	Sequential Operations of Quantum Dot/Photonic Crystal All-Optical Switch With High Repetitive Frequency Pumping. <i>Journal of Lightwave Technology</i> , 2009, 27, 1241-1247.	2.7	26
58	Molecular beam epitaxial growth of site-controlled InAs quantum dot arrays using templates fabricated by the Nano-Jet Probe method. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1794-1796.	1.3	7
59	Selective growth of stacked InAs quantum dots by using the templates formed by the Nano-Jet Probe. <i>Applied Surface Science</i> , 2008, 254, 7821-7823.	3.1	6
60	Selective-area-growth of InAs-QDs with different absorption wavelengths via developed metal-mask/MBE method for integrated optical devices. <i>Applied Surface Science</i> , 2008, 254, 7968-7971.	3.1	8
61	Design and fabrication of nano-photonics-based all-optical flip-flop switch. , 2008, , .		0
62	Optical-Nonlinearity-Induced Phase Shift via Selective-Area Grown InAs Quantum Dots in a Photonic Crystal Waveguide. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 2893-2896.	0.8	2
63	In situ Metal Mask for Selective Area Growth of Thin Epitaxial Layers. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 2987-2990.	0.8	0
64	Topology optimization of a wavelength-selective Y-junction for 2D photonic crystal waveguides. <i>Journal Physics D: Applied Physics</i> , 2008, 41, 175109.	1.3	6
65	Optical flip-flop based on coupled ultra-small Mach-Zehnder all-optical switches. , 2008, , .		3
66	Area-selective and Site-controlled InAs Quantum-dot Growth Techniques for Photonic Crystal-based Ultra-small Integrated Circuit. , 2008, , 405-420.		4
67	Advanced Growth Techniques of InAs-system Quantum Dots for Integrated Nanophotonic Circuits. , 2008, , 529-551.		1
68	Acceleration of the refractive index response in nonlinear photonic crystal / quantum dot waveguides via the Purcell effect. , 2008, , .		0
69	Topology optimization of waveguide bends with wide, flat bandwidth in air-bridge-type photonic crystal slabs. <i>Journal of Applied Physics</i> , 2007, 101, 113108.	1.1	27
70	Topology Optimization for Photonic Crystal Waveguide Bends with Wide and Flat Bandwidths in Air-Bridge type Photonic Crystal Slabs. , 2007, , .		0
71	Fluorescence XAFS Study on Local Structure around Cr Atoms Doped in ZnTe. <i>AIP Conference Proceedings</i> , 2007, , .	0.3	7
72	High transmission recovery of slow light in a photonic crystal waveguide using a hetero groupvelocity waveguide. <i>Optics Express</i> , 2007, 15, 7974.	1.7	38

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73	Measurements of Optical Non-linearity Induced Phase-Shifts of Signal Pulse with Repetitive Control Pulses in Photonic Crystal/Quantum Dot Waveguide. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	3
74	Monolithic growth of InAs-QDs with different absorption wavelengths in different areas for integrated optical devices. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	1
75	Selective Formation of High Density InAs Quantum Dot Arrays Using Templates Fabricated by the Nano-Jet Probe. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
76	InAs Quantum Dots Grown on Selective Areas with a Metal Mask for Photonic-Crystal-Based Ultra-Small and Ultra-Fast All Optical Devices. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
77	Precise control of dry etching for nanometer scale air-hole arrays in two-dimensional GaAs/AlGaAs photonic crystal slabs. Optics Communications, 2007, 275, 257-267.	1.0	22
78	Selective area growth of InAs quantum dots with a metal mask towards optical integrated circuit devices. Journal of Crystal Growth, 2007, 301-302, 771-775.	0.7	20
79	Selective growth of InAs quantum dots using In nano-dot arrays formed by nano-jet probe method. Journal of Crystal Growth, 2007, 301-302, 726-730.	0.7	3
80	Criterion for Removing a Delayed Peak from the Ultrafast Nonlinear Response of Photonic Crystal / Quantum Dot Waveguides. , 2007, , .		0
81	In situ Metal Mask for Selective Area Growth of Thin Epitaxial Layers. , 2007, , .		0
82	Optical-Nonlinearity-Induced Phase Shift via Selective Area Grown InAs-QDs in a Photonic Crystal Waveguide. , 2007, , .		0
83	Photonic Crystals and Quantum Dots: Towards Integrated Optics for Advanced Ultra-Fast All-Optical Signal Processing. , 2006, , .		0
84	Photonic crystal and quantum dot technologies for all-optical switch and logic device. New Journal of Physics, 2006, 8, 208-208.	1.2	126
85	Broadband waveguide intersection with low crosstalk in two-dimensional photonic crystal circuits by using topology optimization. Optics Express, 2006, 14, 9502.	1.7	38
86	New Design for Wide/Flat Bandwidth in Photonic Crystal-Based SMZ All-Optical Device (PC-SMZ). , 2006, , .		0
87	Magneto-optical study of ferromagnetic semiconductor (Zn,Cr)Te. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4102-4105.	0.8	0
88	Topology optimised photonic crystal waveguide intersections with high-transmittance and low crosstalk. Electronics Letters, 2006, 42, 1031.	0.5	9
89	Selective-Area Growth of Self-Assembled InAs-QDs by Metal Mask Method for Optical Integrated Circuit Applications. Materials Research Society Symposia Proceedings, 2006, 959, 1.	0.1	2
90	Topology Optimization for Photonic Crystal Waveguide with Wide and Flat Bandwidths in Ultra-Fast All-Optical Switch (PC-SMZ). , 2006, , .		1

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91	Topology Optimization for Photonic Crystal Waveguide Intersection with Wide and Flat Bandwidths in Ultra-Fast All-Optical Switch (PC-SMZ). , 2006, , .		1
92	Significant Enhancement of Ferromagnetism in Zn <sub>1-x</sub> Cr <sub>x</sub> Te Doped with Iodine as an n-Type Dopant. Physical Review Letters, 2006, 97, 037201.	2.9	47
93	Planar focusing lens grating for vertical coupling on 2D photonic crystal slab waveguide. , 2006, , .		0
94	Growth and magnetic properties of novel ferromagnetic semiconductor (Zn, Cr)Te. Science and Technology of Advanced Materials, 2005, 6, 558-564.	2.8	30
95	Magnetic Behaviors of Ferromagnetic Semiconductor Zn <sub>1-x</sub> Cr <sub>x</sub> Te Grown by MBE. Journal of Superconductivity and Novel Magnetism, 2005, 18, 29-32.	0.5	11
96	Magnetic Properties of undoped and N-doped Zn <sub>1-x</sub> Cr <sub>x</sub> Te Grown by MBE. AIP Conference Proceedings, 2005, , .	0.3	0
97	Growth of silicon nanowires on H-terminated Si {111} surface templates studied by transmission electron microscopy. Microscopy (Oxford, England), 2005, 54, i25-i29.	0.7	7
98	Suppression of ferromagnetism due to hole doping in Zn <sub>1-x</sub> Cr <sub>x</sub> Te grown by molecular-beam epitaxy. Applied Physics Letters, 2005, 87, 192116.	1.5	51
99	Magnetic and structural properties of MBE-grown Zn <sub>1-x</sub> Cr <sub>x</sub> Te films. Journal of Physics Condensed Matter, 2004, 16, S5773-S5776.	0.7	12
100	Nucleation and growth processes of silicon nanowires. Materials Research Society Symposia Proceedings, 2004, 832, 353.	0.1	0
101	Magnetotransport and magnetic properties of p-Zn <sub>1-x</sub> Mn <sub>x</sub> Te: N Carrier-induced ferromagnetism. Physica Status Solidi (B): Basic Research, 2004, 241, 668-671.	0.7	2
102	Magnetic properties of MBE-grown Zn <sub>1-x</sub> Cr <sub>x</sub> Te. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 957-960.	0.8	26
103	Misleading fringes in TEM images and diffraction patterns of Si nanocrystallites. Crystal Research and Technology, 2003, 38, 1082-1086.	0.6	31
104	Formation mechanism of nanocatalysts for the growth of silicon nanowires on a hydrogen-terminated Si {111} surface template. Applied Physics Letters, 2003, 82, 979-981.	1.5	19
105	Novel amorphization process in silicon induced by electron irradiation. Journal of Non-Crystalline Solids, 2002, 299-302, 793-797.	1.5	0
106	Observation of silicon surface nanoholes by scanning tunneling microscopy. Surface Science, 2001, 493, 547-554.	0.8	11
107	Fabrication of periodic nanohole multilayer structure on silicon surface toward photonic crystal. Physica B: Condensed Matter, 2001, 308-310, 1222-1225.	1.3	1
108	Optical properties of Si nanowires on a Si {111} surface. Materials Research Society Symposia Proceedings, 1999, 588, 98.	0.1	4

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109	Silicon nanowhiskers grown on a hydrogen-terminated silicon {111} surface. Applied Physics Letters, 1998, 73, 3700-3702.	1.5	123
110	VLS Growth of Si nanowhiskers on a H-terminated Si{111} surface. Materials Research Society Symposia Proceedings, 1998, 536, 305.	0.1	1
111	Application of Liquid Laser Ablation: Organic Nanoparticle Formation and Hydrogen Gas Generation. , 0, , .		0
112	OCT with a Visible Broadband Light Source Applied to High-Resolution Nondestructive Inspection for Semiconductor Optical Devices. , 0, , .		0